

ABSTRACT OF THE DISCLOSURE

A method of forming a low temperature polysilicon thin film transistor includes steps of: providing a substrate; forming a polysilicon layer on the substrate; forming a gate oxide layer on the polysilicon layer; forming a photoresist pattern on the gate oxide layer; using the photoresist pattern as a mask and etching the gate oxide layer and the polysilicon layer; removing the photoresist pattern; forming a gate on the gate oxide layer; and implanting dopants to form source/drain region by using the gate as a mask.

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